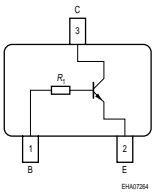


NPN Silicon Digital Transistor

- Switching circuit, inverter, interface circuit, driver circuit
- Built in bias resistor ($R_1=22k\Omega$)


BCR139/F/L3
BCR139T


Type	Marking	Pin Configuration						Package
		1=B	2=E	3=C	-	-	-	
BCR139	WYs	1=B	2=E	3=C	-	-	-	SOT23
BCR139F	WYs	1=B	2=E	3=C	-	-	-	TSFP-3
BCR139L3	WY	1=B	2=E	3=C	-	-	-	TSLP-3-4
BCR139T	WYs	1=B	2=E	3=C	-	-	-	SC75

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	50	V
Collector-base voltage	V_{CBO}	50	
Emitter-base voltage	V_{EBO}	5	
Input on voltage	$V_{i(on)}$	30	
Collector current	I_C	100	mA
Total power dissipation- BCR139, $T_S \leq 102^\circ\text{C}$ BCR139F, $T_S \leq 128^\circ\text{C}$ BCR139L3, $T_S \leq 135^\circ\text{C}$ BCR139T, $T_S \leq 109^\circ\text{C}$	P_{tot}	200 250 250 250	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}		K/W
BCR139		≤ 240	
BCR139F		≤ 90	
BCR139L3		≤ 60	
BCR139T		≤ 165	

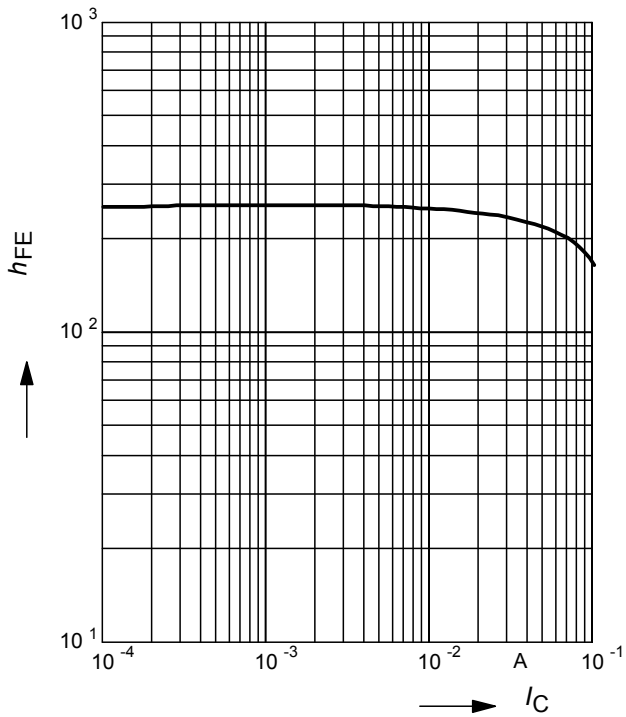
¹For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 100 \mu\text{A}, I_B = 0$	$V_{(BR)CEO}$	50	-	-	V
Collector-base breakdown voltage $I_C = 10 \mu\text{A}, I_E = 0$	$V_{(BR)CBO}$	50	-	-	
Emitter-base breakdown voltage $I_E = 10 \mu\text{A}, I_C = 0$	$V_{(BR)EBO}$	5	-	-	
Collector-base cutoff current $V_{CB} = 40 \text{ V}, I_E = 0$	I_{CBO}	-	-	100	nA
DC current gain ¹⁾ $I_C = 5 \text{ mA}, V_{CE} = 5 \text{ V}$	h_{FE}	120	-	630	-
Collector-emitter saturation voltage ¹⁾ $I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$	V_{CEsat}	-	-	0.3	V
Input off voltage $I_C = 100 \mu\text{A}, V_{CE} = 5 \text{ V}$	$V_{i(off)}$	0.4	-	0.8	
Input on voltage $I_C = 2 \text{ mA}, V_{CE} = 0.3 \text{ V}$	$V_{i(on)}$	0.5	-	1.1	
Input resistor	R_1	15	22	29	k Ω
¹⁾ Pulse test: $t < 300 \mu\text{s}$; $D < 2\%$					
AC Characteristics					
Transition frequency $I_C = 10 \text{ mA}, V_{CE} = 5 \text{ V}, f = 100 \text{ MHz}$	f_T	-	150	-	MHz
Collector-base capacitance $V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}$	C_{cb}	-	3	-	pF

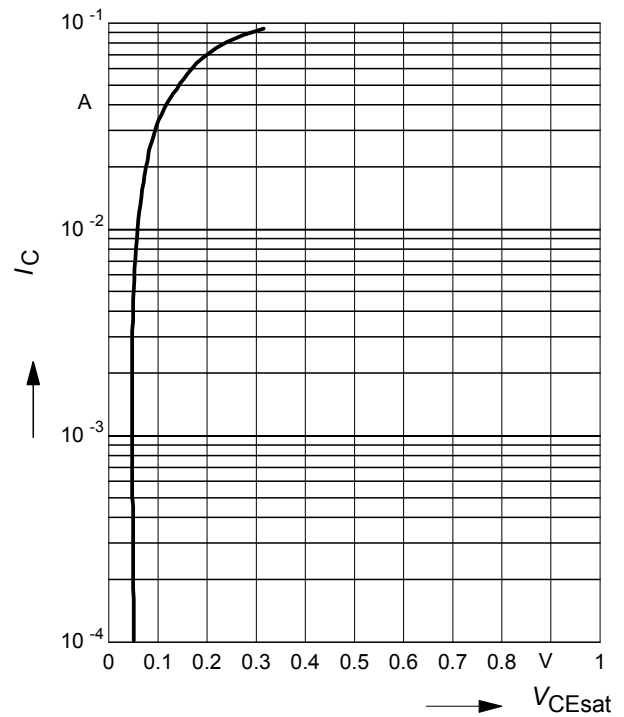
DC current gain $h_{FE} = f(I_C)$

$V_{CE} = 5V$ (common emitter configuration)



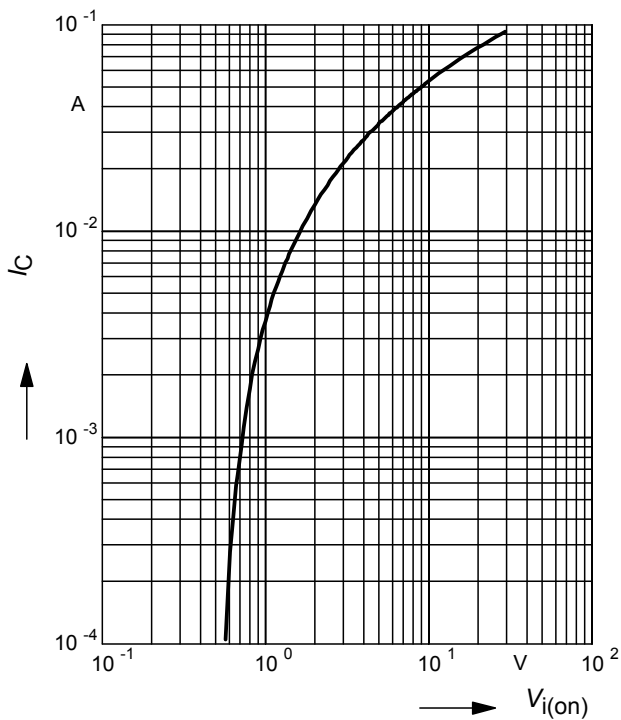
Collector-emitter saturation voltage

$V_{CEsat} = f(I_C), h_{FE} = 20$



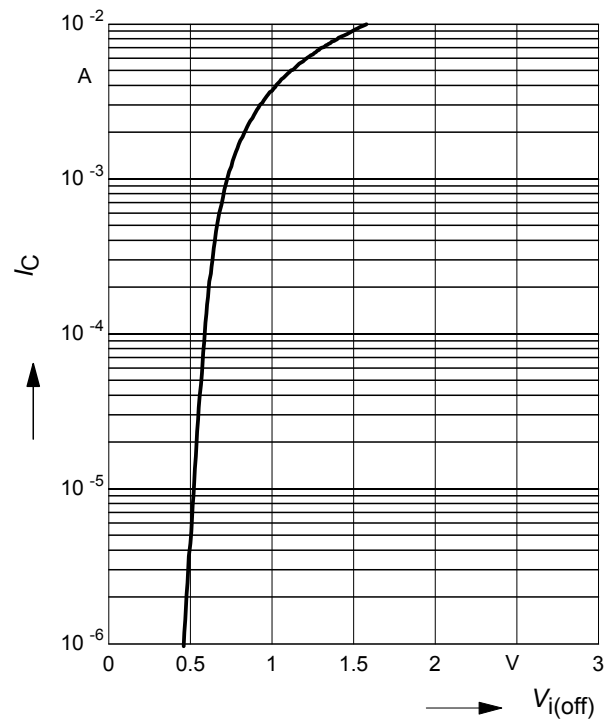
Input on Voltage $V_{i(on)} = f(I_C)$

$V_{CE} = 0.3V$ (common emitter configuration)



Input off voltage $V_{i(off)} = f(I_C)$

$V_{CE} = 5V$ (common emitter configuration)



Total power dissipation $P_{tot} = f(T_S)$

BCR139



Total power dissipation $P_{tot} = f(T_S)$

BCR139F



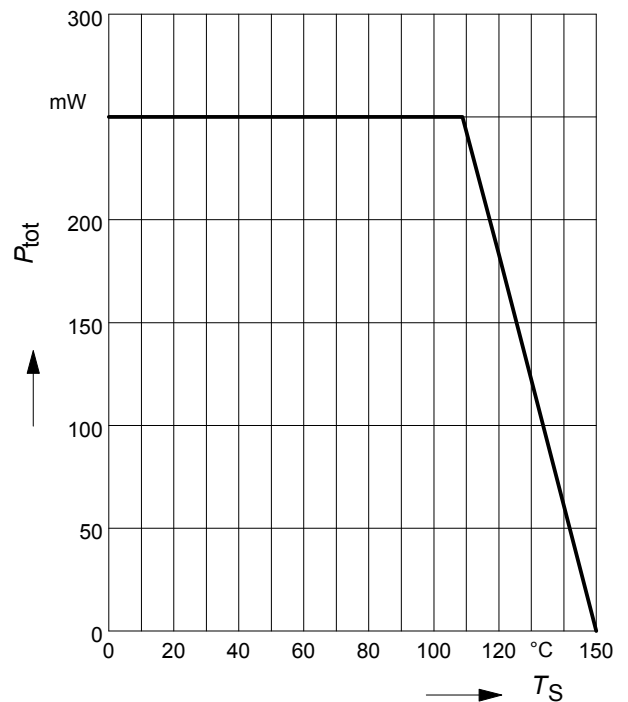
Total power dissipation $P_{tot} = f(T_S)$

BCR139L3



Total power dissipation $P_{tot} = f(T_S)$

BCR139T



Permissible Pulse Load $R_{thJS} = f(t_p)$

BCR139



Permissible Pulse Load

$P_{totmax}/P_{totDC} = f(t_p)$

BCR139



Permissible Puls Load $R_{thJS} = f(t_p)$

BCR139F



Permissible Pulse Load

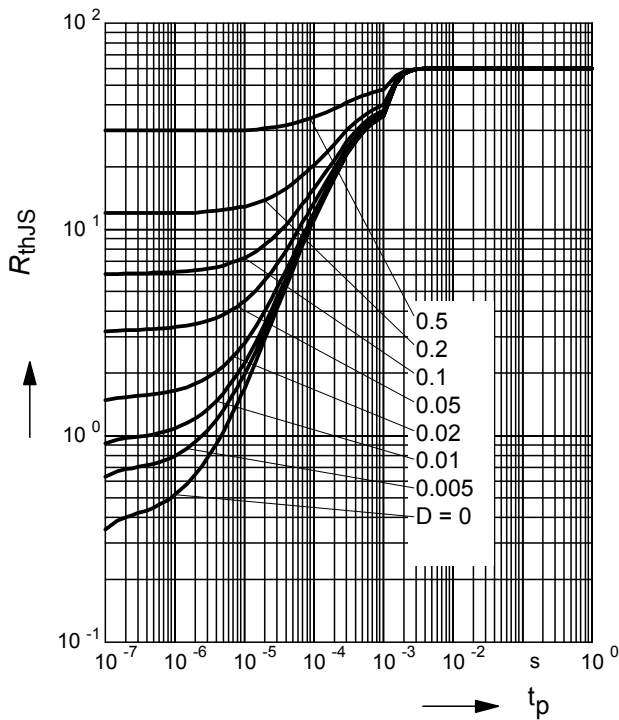
$P_{totmax}/P_{totDC} = f(t_p)$

BCR139F



Permissible Puls Load $R_{thJS} = f(t_p)$

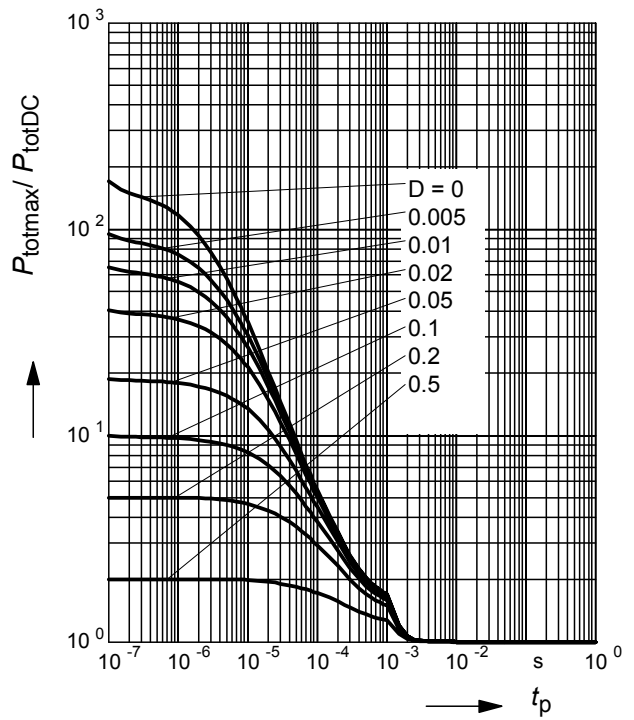
BCR139L3



Permissible Pulse Load

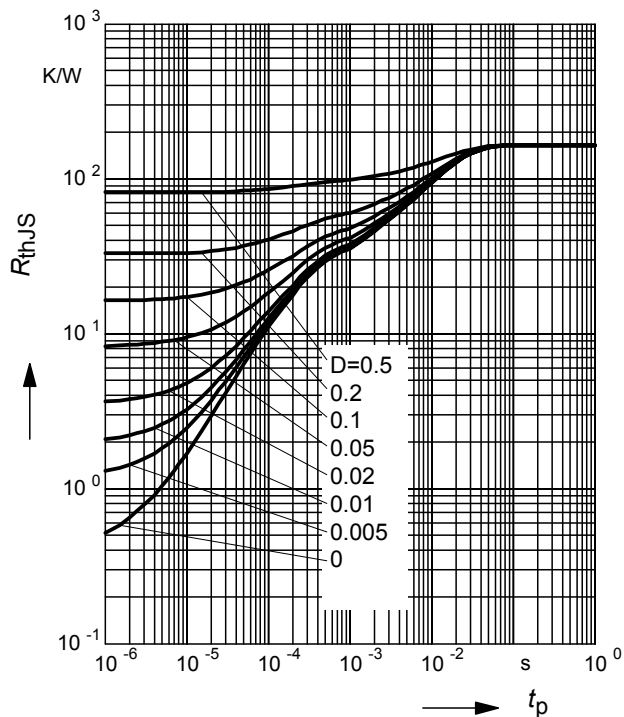
$P_{totmax}/P_{totDC} = f(t_p)$

BCR139L3



Permissible Puls Load $R_{thJS} = f(t_p)$

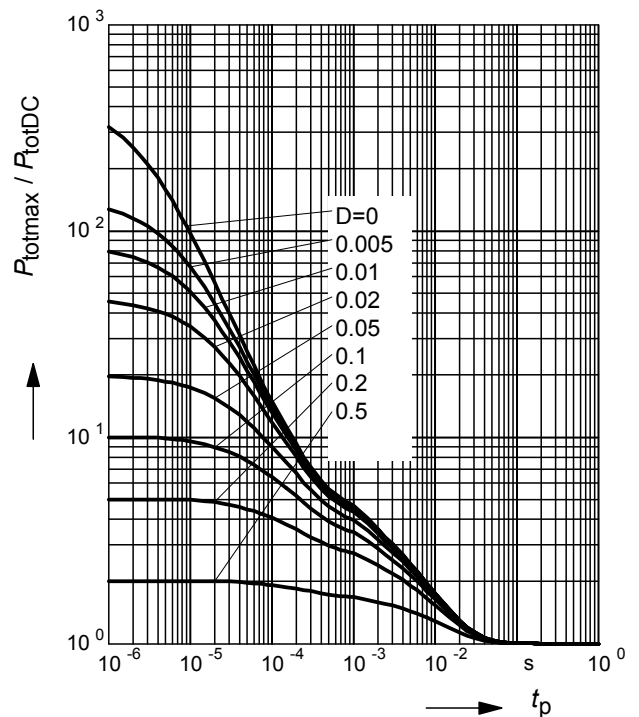
BCR139T



Permissible Pulse Load

$P_{totmax}/P_{totDC} = f(t_p)$

BCR139T



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